

Substitute for form 1449/PTO				<i>Complete if Known</i>	
				Application Number	10/537,804
				Filing Date	June 7, 2005
				First Named Inventor	Robert DWILINSKI
				Art Unit	1792
				Examiner Name	F. C. Hiteshew
Sheet	1	of	3	Attorney Docket Number 204552035400	

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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/537,804
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Sheet	2	of	3	First Named Inventor	Robert DWILINSKI
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				Examiner Name	F. C. Hiteshew
				Attorney Docket Number 204552035400	

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NON PATENT LITERATURE DOCUMENTS				
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
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Examiner Signature	Date Considered
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